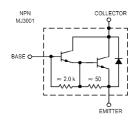
# NPN Silicon Darlington Medium Power Transistor multicomp PRO VCEO 80V, IC 10A, 150W, TO-3







### **Features**

- 1. High DC Current Gain h<sub>FE</sub> = 4000 (Typ.) @ l<sub>c</sub>=25A DC h<sub>FE</sub> = 400 (Min) @ l<sub>c</sub>= 5 Adc
- 2. Monolithic Construction with Built-In Base-Emitter Shunt Resistor

**APPLICATIONS:** For use as output devices in complementary general purpose amplifier applications.

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

Rating	Symbol	Max	Units
Collector-Emitter Voltage	Vceo	80	V DC
Collector-Base Voltage	VcB	80	V DC
Emitter Base Voltage	VEB	5	V DC
Collector Current	Ic	10	Adc
Base Current	lв	0.2	Adc
Total Device Dissipation @ TC 25°C Derate above 25°C	Po	150 0.857	Watts W/°C
Operating and Storage Junction Temperature Range	TJ, Tstg	-55°C to +200°C	°C

### **Thermal Characteristics**

Characteristic	Symbol	Rating	Unit
Thermal Resistance, Junction to case	JC	1.17	°C/W





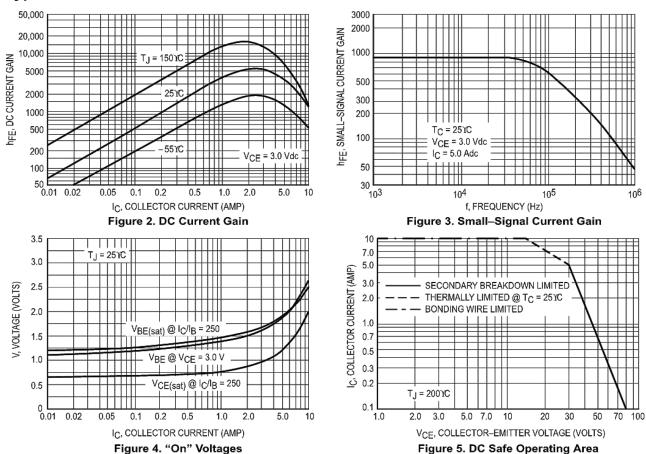
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## Electrical Characteristics at TA = 25°C unless otherwise specified)

Description	Symbol	Min	Max	Units
Off Characteristics	•	•		•
Collector-Emitter Breakdown Voltage (1) (Ic = 100mADC, I <sub>B</sub> = 0)	V(BR)CEO	80	-	V DC
Collector-Emitter Leakage Current (Vce = 80V DC, RBE = 1k $\Omega$ (Vce = 80V DC, RBE = 1k $\Omega$ , Tc = 150°C)	Icer		1 5	mA DC
Emitter Cut Off Current (VBE = 5V DC, Ic = 0)	ІЕВО	-	5	mA DC
Collector-Emitter Leakage Current (VcE = 40V DC, IB = 0)	ICEO	-	1	mA DC
On Characteristics (1)	•	•	•	
DC Current Gain (Ic = 5A DC, VcE = 3 Vcc	hfe	1000	-	-
Collector-Emitter Saturation Voltage (Ic = 5A DC, I <sub>B</sub> = 20 mA <sub>DC</sub> (Ic = 10A DC, I <sub>B</sub> = 50 mA <sub>DC</sub>	VCE(sat)		2 4	V DC
Base-Emitter Voltage (Ic = 5A DC, VcE = 3 Vcc	VBE(on)	-	3	V DC

<sup>(1)</sup> Pulse Test: Pulse Width = 300µs, Duty Cycle = 2%

# **Typical Characteristics Curves**

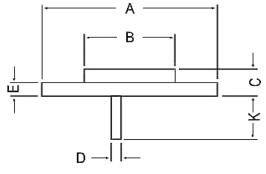


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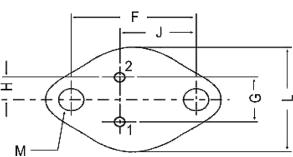


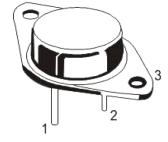
# NPN Silicon Darlington Medium Power Transistor multicomp PRO

### **Package Details**



Dimensions: Millimetres





PIN CONFIGURATION

- 1. BASE
- 2. EMITTER
- 3. COLLECTOR

Dim	Min.	Max.
Α	-	39.37
В	-	22.22
С	6.35	8.5
D	0.96	1.09
Е	1	1.77
F	29.9	30.4
G	10.69	11.18
Н	5.2	5.72
J	16.64	17.15
K	11.15	12.25
L	-	26.67
M	3.84	4.19

#### **Part Number Table**

Description	Part Number	
Silicon Darlington Medium Power Transistor, NPN 80V, 10A, TO-3	MJ3001	

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